

Title (en)  
ETCHING PROCESS

Title (de)  
ÄTZVERFAHREN

Title (fr)  
PROCESSUS DE GRAVURE

Publication  
**EP 3075003 A1 20161005 (EN)**

Application  
**EP 14825103 A 20141119**

Priority  
• EP 13194774 A 20131128  
• EP 2014075023 W 20141119  
• EP 14825103 A 20141119

Abstract (en)  
[origin: EP2879165A1] Processes for the manufacture of devices including microelectromechanical systems comprising a step in which a substrate is etched using an etching agent prepared from SF<sub>4</sub> are disclosed.

IPC 8 full level  
**H01L 21/3065** (2006.01); **C23C 16/44** (2006.01); **C23F 1/00** (2006.01)

CPC (source: EP)  
**C23F 4/00** (2013.01); **H01L 21/3065** (2013.01); **H01L 21/3116** (2013.01); **H01L 21/32136** (2013.01)

Citation (search report)  
See references of WO 2015078749A1

Citation (examination)  
PATEAU AMAND ET AL: "Modeling of inductively coupled plasma SF<sub>6</sub>/O<sub>2</sub>/Ar plasma discharge: Effect of O<sub>2</sub> on the plasma kinetic properties", JOURNAL OF VACUUM SCIENCE AND TECHNOLOGY: PART A, AVS /AIP, MELVILLE, NY., US, vol. 32, no. 2, 1 January 1901 (1901-01-01), XP012184288, ISSN: 0734-2101, [retrieved on 19010101], DOI: 10.1116/1.4853675

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Designated extension state (EPC)  
BA ME

DOCDB simple family (publication)  
**EP 2879165 A1 20150603**; EP 3075003 A1 20161005; WO 2015078749 A1 20150604

DOCDB simple family (application)  
**EP 13194774 A 20131128**; EP 14825103 A 20141119; EP 2014075023 W 20141119